Silicon Carbide Power Schottky Diode Chip

Features

- 650 V Schottky rectifier
- 250 °C maximum operating temperature
- Temperature independent switching behavior
- Superior surge current capability
- Positive temperature coefficient of V_F
- Extremely fast switching speeds
- Superior figure of merit Q_C/I_F

Maximum Ratings at T_j = 250 °C, unless otherwise specified

Parameter	Symbol	Conditions	Values	Unit
Repetitive peak reverse voltage	V_{RRM}		650	V
Continuous forward current	I_F	$T_C \le 235$ °C	1	A
RMS forward current	$I_{F(RMS)}$	$T_C \le 235$ °C	2	A
Operating and storage temperature	T_j , T_{stg}		-55 to 250	°C

Electrical Characteristics at T_j = 250 °C, unless otherwise specified

Parameter	Symbol	Conditions		Values			Unit
				min.	typ.	max.	
Diode forward voltage	V_F	I_F = 1 A, T_j = 25 °C I_F = 1 A, T_j = 210 °C			1.5 2.3		V
Reverse current	I_R	V_R = 650 V, T_j = 25 °C V_R = 650 V, T_j = 250 °C			0.03 1.7	5 20	µA
Total capacitive charge	Q_C	$I_F \le I_{F,MAX}$ dI_F/dt = 200 A/µs T_j = 210 °C	V_R = 400 V		7		nC
Switching time	t_s		V_R = 400 V		< 17		ns
Total capacitance	C	V_R = 1 V, f = 1 MHz, T_j = 25 °C V_R = 400 V, f = 1 MHz, T_j = 25 °C V_R = 800 V, f = 1 MHz, T_j = 25 °C			76 12 11		pF

Thermal Characteristics

Thermal resistance, junction - case	R_{thJC}	Assuming TO-276 package		3.55	°C/W

***For chip size and metallization, please refer to the mechanical datasheet (must have a non-disclosure agreement with GeneSiC Semiconductor).**

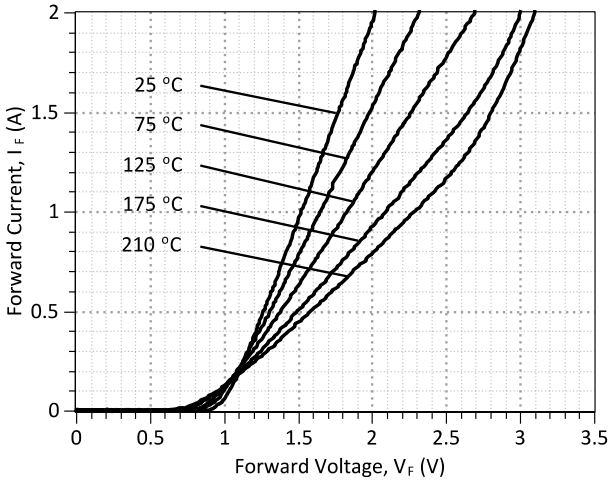

Figure 1: Typical Forward Characteristics

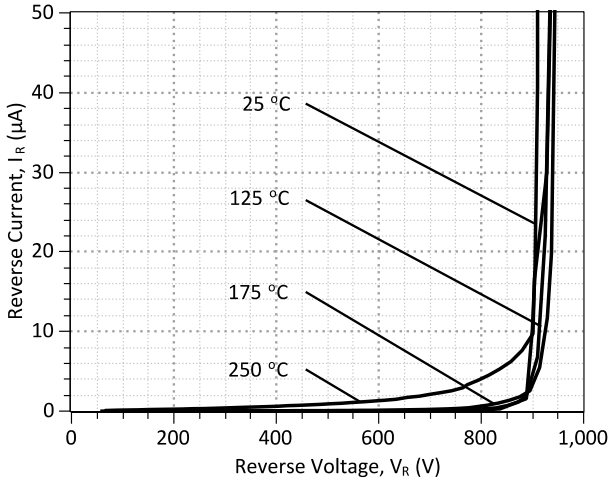

Figure 2: Typical Reverse Characteristics

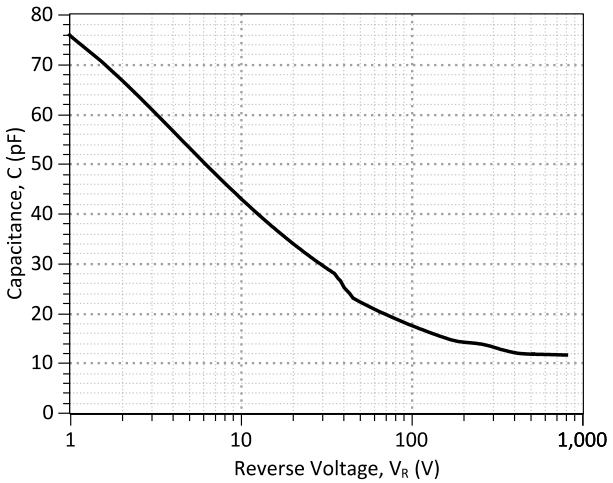

Figure 3: Typical Junction Capacitance vs Reverse Voltage Characteristics

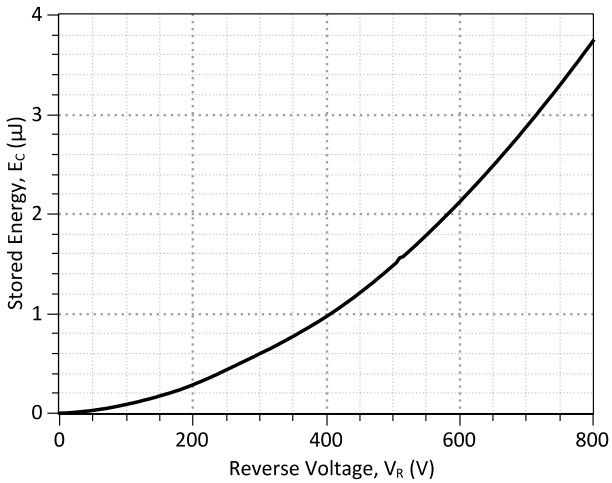

Figure 4: Typical Switching Energy vs Reverse Voltage Characteristics

Revision History			
Date	Revision	Comments	Supersedes
2012/04/03	0	Initial release	

Published by
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43670 Trade Center Place Suite 155
Dulles, VA 20166

SPICE Model Parameters

Copy the following code into a SPICE software program for simulation of the GB01SHT06-CAL device.

```
*     MODEL OF GeneSiC Semiconductor Inc.
*
*     $Revision:   1.0           $
*     $Date:   05-SEP-2013       $
*
*     GeneSiC Semiconductor Inc.
*     43670 Trade Center Place Ste. 155
*     Dulles, VA 20166
*     httphttp://www.genesicsemi.com/index.php/sic-products/schottky
*
*     COPYRIGHT (C) 2013 GeneSiC Semiconductor Inc.
*     ALL RIGHTS RESERVED
*
* These models are provided "AS IS, WHERE IS, AND WITH NO WARRANTY
* OF ANY KIND EITHER EXPRESSED OR IMPLIED, INCLUDING BUT NOT LIMITED
* TO ANY IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A
* PARTICULAR PURPOSE."
* Models accurate up to 2 times rated drain current.
*
* Start of GB01SHT06-CAL SPICE Model
*
.SUBCKT GB01SHT06 ANODE KATHODE
D1 ANODE KATHODE GB01SHT06_25C; Call the Schottky Diode Model
D2 ANODE KATHODE GB01SHT06_PIN; Call the PiN Diode Model
.MODEL GB01SHT06_25C D
+ IS       3.57E-18         RS         0.49751
+ TRS1     0.0057           TRS2       2.40E-05
+ N        1                IKF        322
+ EG       1.2              XTI        3
+ CJO      9.12E-11         VJ         0.371817384
+ M        1.527759838      FC         0.5
+ TT       1.00E-10         BV         800
+ IBV      1.00E-03         VPK        650
+ IAVE     1                TYPE       SiC_Schottky
+ MFG      GeneSiC_Semiconductor
.MODEL GB01SHT06_PIN D
+ IS       5.73E-11         RS         0.72994
+ N        5                IKF        800
+ EG       3.23             XTI        -14
+ FC       0.5              TT         0
+ BV       800              IBV        1.00E-03
+ VPK      650              IAVE       1
+ TYPE     SiC_PiN
.ENDS
*
* End of GB01SHT06-CAL SPICE Model
```